

Schottky Barrier Diode

PIN	DESCRIPTION
1	Cathode
2	Anode



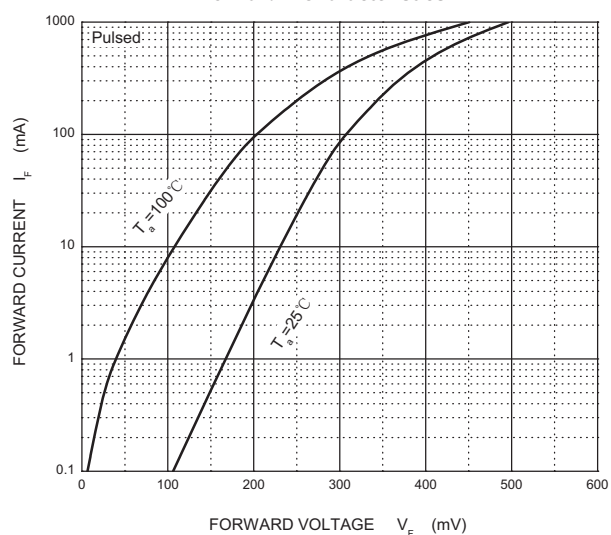
Simplified outline SOD-123 and symbol

MARKING: RB160M-30: 73
RB160M-40: 74
RB160M-60: 76
RB160M-90: 83

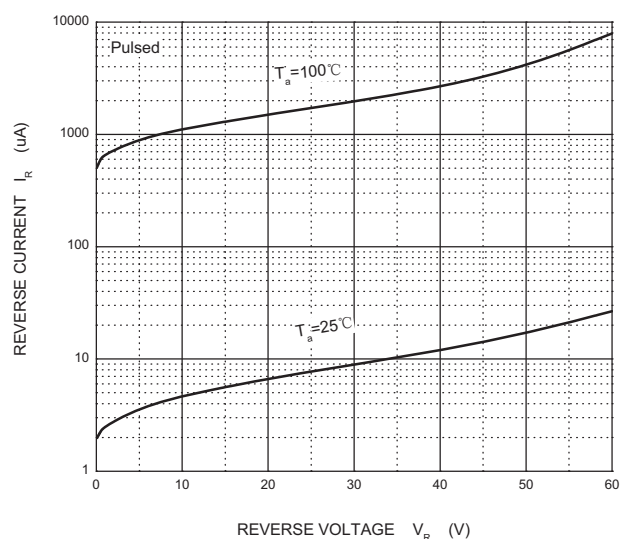
Parameter	Symbols	RB160M-30	RB160M-40	RB160M-60	RB160M-90	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	30	40	60	90	V
Maximum RMS voltage	V_{RMS}	21	28	42	63	V
Maximum DC Blocking Voltage	V_{DC}	30	40	60	90	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0				A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	40			30	A
Max Instantaneous Forward Voltage at 1 A	V_F	0.55		0.70	0.85	V
Maximum DC Reverse Current $T_a = 25^{\circ}\text{C}$ at Rated DC Reverse Voltage $T_a = 100^{\circ}\text{C}$	I_R	0.3 10			0.2 5	mA
Typical Junction Capacitance ¹⁾	C_j	110	80			pF
Typical Thermal Resistance ²⁾	$R_{\theta JA}$	115				$^{\circ}\text{C/W}$
Operating Junction Temperature Range	T_j	-55 ~ +125				$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150				$^{\circ}\text{C}$

Typical Characteristics

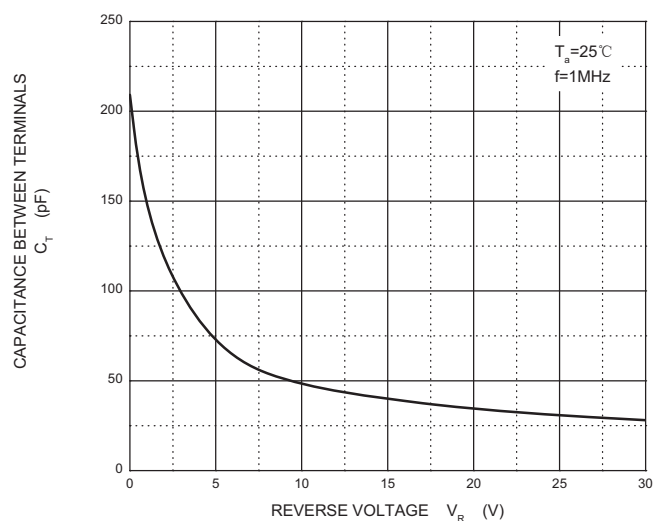
Forward Characteristics



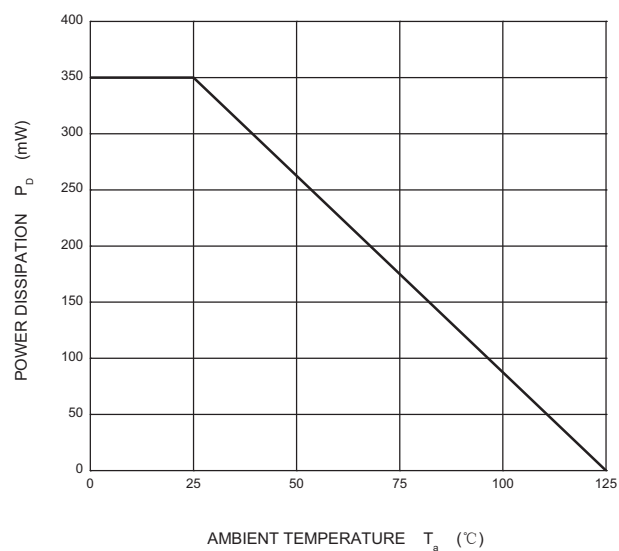
Reverse Characteristics



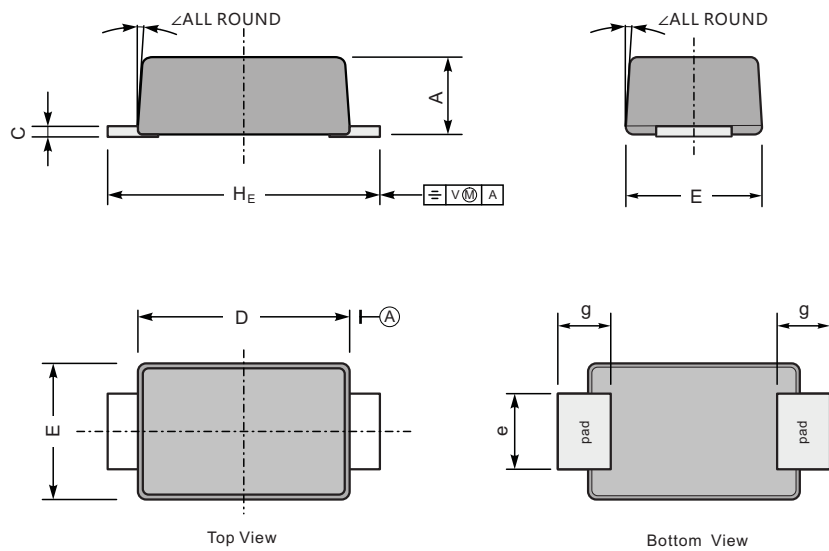
Capacitance Characteristics



Power Derating Curve



PACKAGE OUTLINE



UNIT		A	C	D	E	e	g	H _E	7°
mm	max	1.1	0.20	2.9	1.9	1.1	0.9	3.8	7°
	min	0.9	0.12	2.6	1.7	0.8	0.7	3.5	
mil	max	43	7.9	114	75	43	35	150	
	min	35	4.7	102	67	31	28	138	